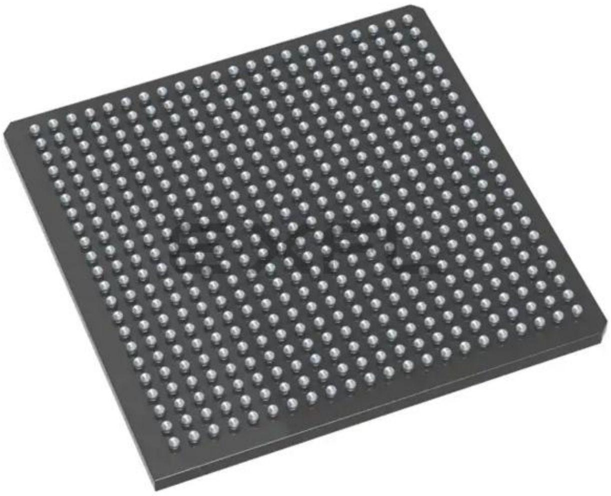

Welcome to E-XFL.COM

Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	-
Total RAM Bits	276480
Number of I/O	223
Number of Gates	1500000
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	484-BGA
Supplier Device Package	484-FPBGA (23x23)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/p1afs1500-2fg484i

Instant On

Flash-based Fusion devices are Level 0 Instant On. Instant On Fusion devices greatly simplify total system design and reduce total system cost by eliminating the need for CPLDs. The Fusion Instant On clocking (PLLs) replaces off-chip clocking resources. The Fusion mix of Instant On clocking and analog resources makes these devices an excellent choice for both system supervisor and system management functions. Instant On from a single 3.3 V source enables Fusion devices to initiate, control, and monitor multiple voltage supplies while also providing system clocks. In addition, glitches and brownouts in system power will not corrupt the Fusion device flash configuration. Unlike SRAM-based FPGAs, the device will not have to be reloaded when system power is restored. This enables reduction or complete removal of expensive voltage monitor and brownout detection devices from the PCB design.

Flash-based Fusion devices simplify total system design and reduce cost and design risk, while increasing system reliability.

Firm Errors

Firm errors occur most commonly when high-energy neutrons, generated in the upper atmosphere, strike a configuration cell of an SRAM FPGA. The energy of the collision can change the state of the configuration cell and thus change the logic, routing, or I/O behavior in an unpredictable way. Another source of radiation-induced firm errors is alpha particles. For an alpha to cause a soft or firm error, its source must be in very close proximity to the affected circuit. The alpha source must be in the package molding compound or in the die itself. While low-alpha molding compounds are being used increasingly, this helps reduce but does not entirely eliminate alpha-induced firm errors.

Firm errors are impossible to prevent in SRAM FPGAs. The consequence of this type of error can be a complete system failure. Firm errors do not occur in Fusion flash-based FPGAs. Once it is programmed, the flash cell configuration element of Fusion FPGAs cannot be altered by high-energy neutrons and is therefore immune to errors from them.

Recoverable (or soft) errors occur in the user data SRAMs of all FPGA devices. These can easily be mitigated by using error detection and correction (EDAC) circuitry built into the FPGA fabric.

Low Power

Flash-based Fusion devices exhibit power characteristics similar to those of an ASIC, making them an ideal choice for power-sensitive applications. With Fusion devices, there is no power-on current surge and no high current transition, both of which occur on many FPGAs.

Fusion devices also have low dynamic power consumption and support both low power standby mode and very low power sleep mode, offering further power savings.

Advanced Flash Technology

The Fusion family offers many benefits, including nonvolatility and reprogrammability through an advanced flash-based, 130-nm LVCMOS process with seven layers of metal. Standard CMOS design techniques are used to implement logic and control functions. The combination of fine granularity, enhanced flexible routing resources, and abundant flash switches allows very high logic utilization (much higher than competing SRAM technologies) without compromising device routability or performance. Logic functions within the device are interconnected through a four-level routing hierarchy.

Erase Page Operation

The Erase Page operation is initiated when the ERASEPAGE pin is asserted. The Erase Page operation allows the user to erase (set user data to zero) any page within the FB.

The use of the OVERWRITEPAGE and PAGELOSSPROTECT pins is the same for erase as for a Program Page operation.

As with the Program Page operation, a STATUS of '01' indicates that the addressed page is not erased.

A waveform for an Erase Page operation is shown in Figure 2-37.

Erase errors include the following:

1. Attempting to erase a page that is Overwrite Protected (STATUS = '01')
2. Attempting to erase a page that is not in the Page Buffer when the Page Buffer has entered Page Loss Protection mode (STATUS = '01')
3. The Write Count of the erased page exceeding the Write Threshold defined in the part specification (STATUS = '11')
4. The ECC Logic determining that there is an uncorrectable error within the erased page (STATUS = '10')

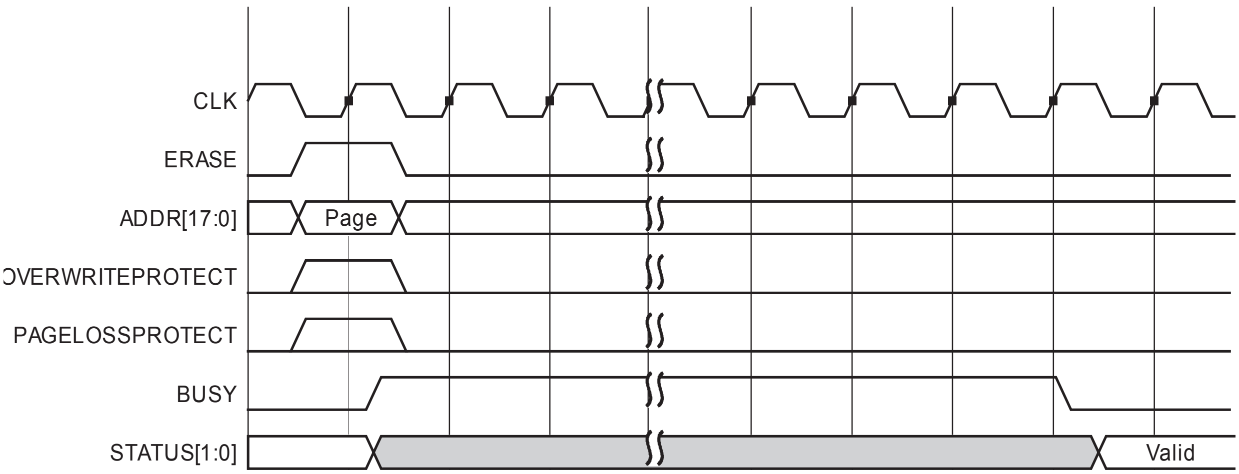

***Figure 2-37* • FB Erase Page Waveform**

SRAM Characteristics

Timing Waveforms

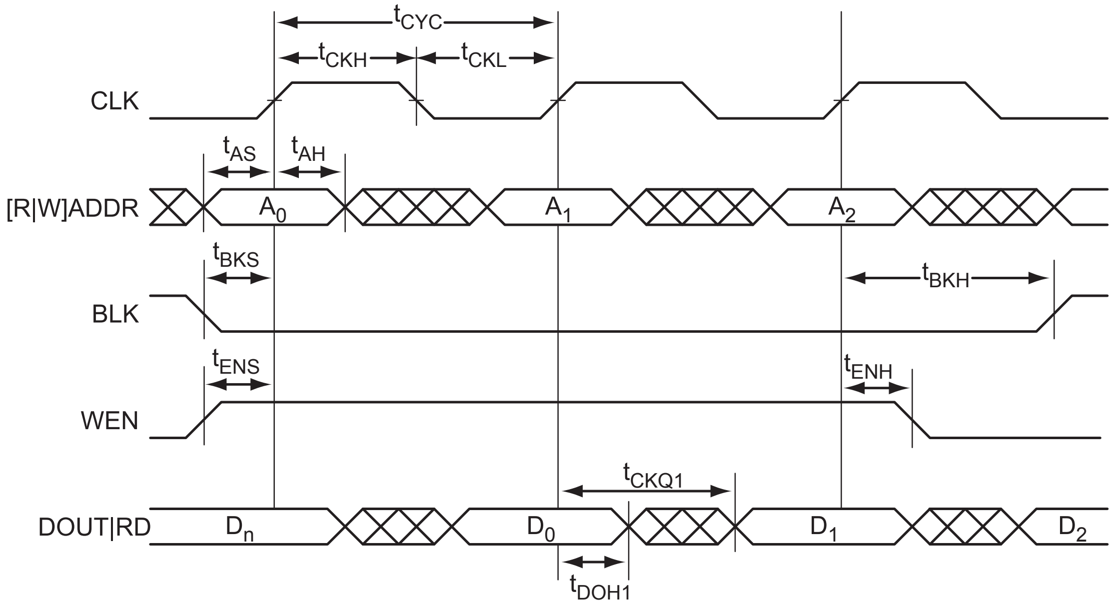

Figure 2-50 • **RAM Read for Flow-Through Output. Applicable to both RAM4K9 and RAM512x18.**

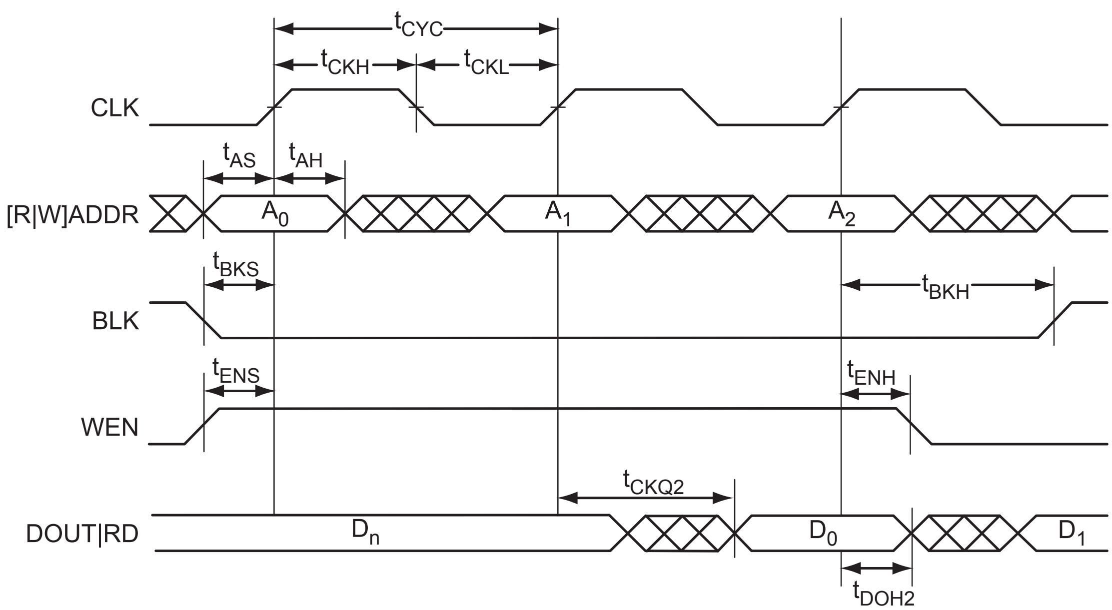

Figure 2-51 • **RAM Read for Pipelined Output. Applicable to both RAM4K9 and RAM512x18.**

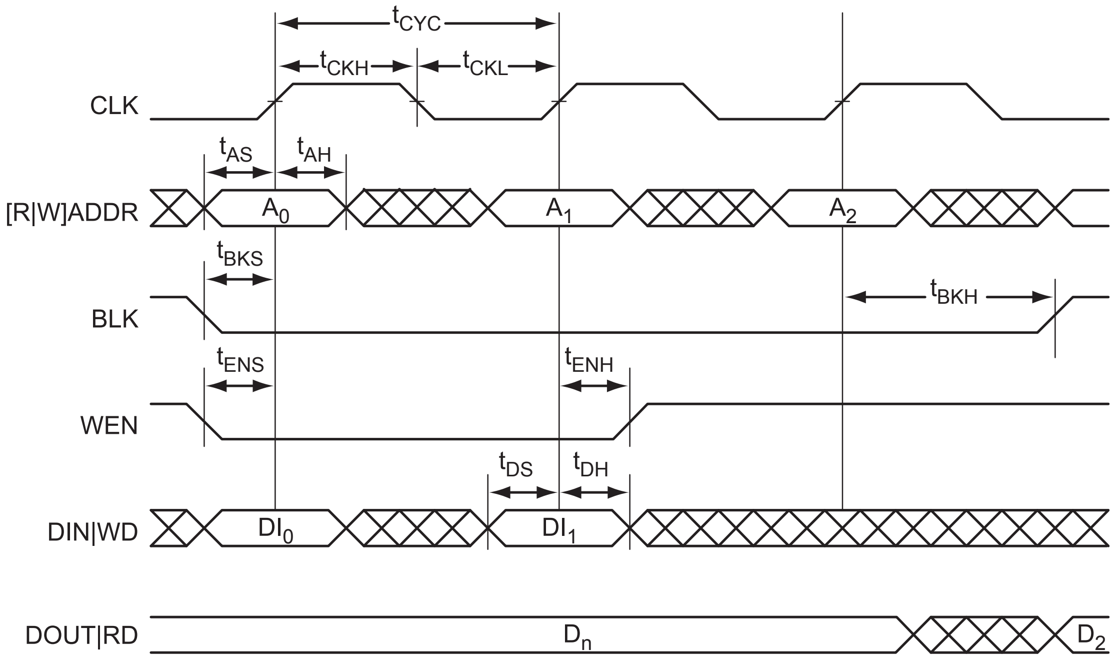

Figure 2-52 • **RAM Write, Output Retained. Applicable to both RAM4K9 and RAM512x18.**

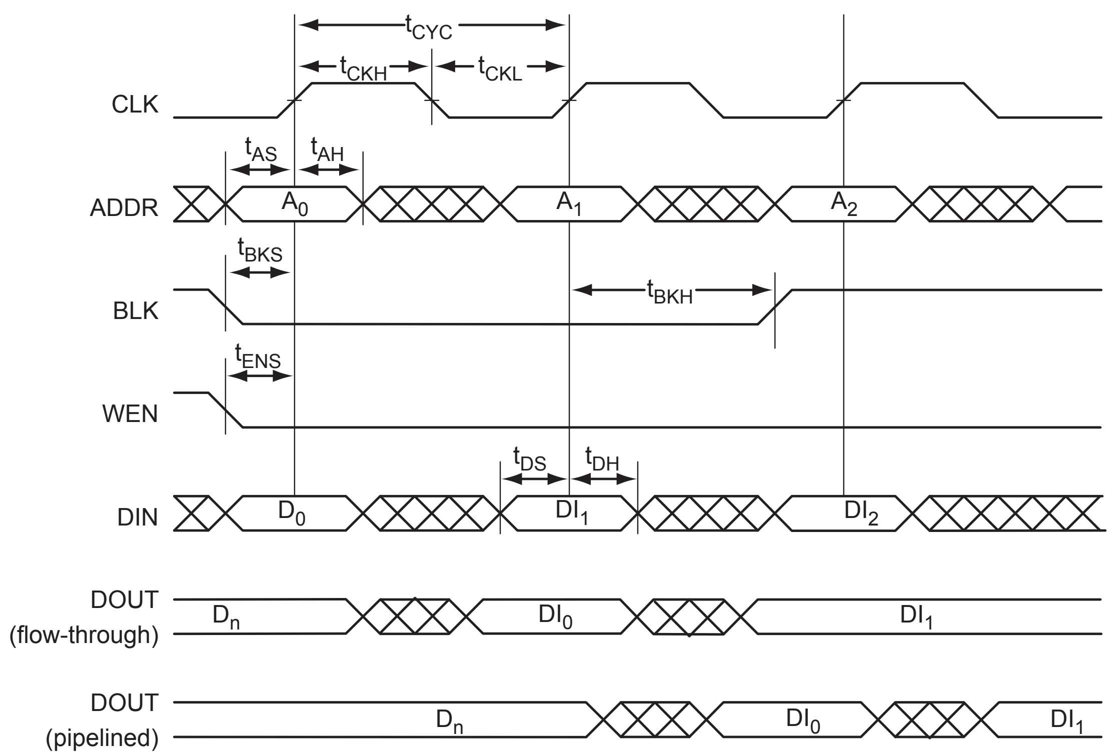

Figure 2-53 • **RAM Write, Output as Write Data (WMODE = 1). Applicable to RAM4K9 Only.**

Table 2-36 describes each pin in the Analog Block. Each function within the Analog Block will be explained in detail in the following sections.

***Table 2-36* • Analog Block Pin Description**

Signal Name	Number of Bits	Direction	Function	Location of Details
VAREF	1	Input/Output	Voltage reference for ADC	ADC
ADCGNDREF	1	Input	External ground reference	ADC
MODE[3:0]	4	Input	ADC operating mode	ADC
SYSCLK	1	Input	External system clock	
TVC[7:0]	8	Input	Clock divide control	ADC
STC[7:0]	8	Input	Sample time control	ADC
ADCSTART	1	Input	Start of conversion	ADC
PWRDWN	1	Input	ADC comparator power-down if 1. When asserted, the ADC will stop functioning, and the digital portion of the analog block will continue operating. This may result in invalid status flags from the analog block. Therefore, Microsemi does not recommend asserting the PWRDWN pin.	ADC
ADCRESET	1	Input	ADC resets and disables Analog Quad – active high	ADC
BUSY	1	Output	1 – Running conversion	ADC
CALIBRATE	1	Output	1 – Power-up calibration	ADC
DATAVALID	1	Output	1 – Valid conversion result	ADC
RESULT[11:0]	12	Output	Conversion result	ADC
TMSTBINT	1	Input	Internal temp. monitor strobe	ADC
SAMPLE	1	Output	1 – An analog signal is actively being sampled (stays high during signal acquisition only) 0 – No analog signal is being sampled	ADC
VAREFSEL	1	Input	0 = Output internal voltage reference (2.56 V) to VAREF 1 = Input external voltage reference from VAREF and ADCGNDREF	ADC
CHNUMBER[4:0]	5	Input	Analog input channel select	Input multiplexer
ACMCLK	1	Input	ACM clock	ACM
ACMWEN	1	Input	ACM write enable – active high	ACM
ACMRESET	1	Input	ACM reset – active low	ACM
ACMWDATA[7:0]	8	Input	ACM write data	ACM
ACMRDATA[7:0]	8	Output	ACM read data	ACM
ACMADDR[7:0]	8	Input	ACM address	ACM
CMSTB0 to CMSTB9	10	Input	Current monitor strobe – 1 per quad, active high	Analog Quad

Channel Input Offset Error

Channel Offset error is measured as the input voltage that causes the transition from zero to a count of one. An Ideal Prescaler will have offset equal to ½ of LSB voltage. Offset error is a positive or negative when the first transition point is higher or lower than ideal. Offset error is expressed in LSB or input voltage.

Total Channel Error

Total Channel Error is defined as the total error measured compared to the ideal value. Total Channel Error is the sum of gain error and offset error combined. Figure 2-68 shows how Total Channel Error is measured.

Total Channel Error is defined as the difference between the actual ADC output and ideal ADC output. In the example shown in Figure 2-68, the Total Channel Error would be a negative number.

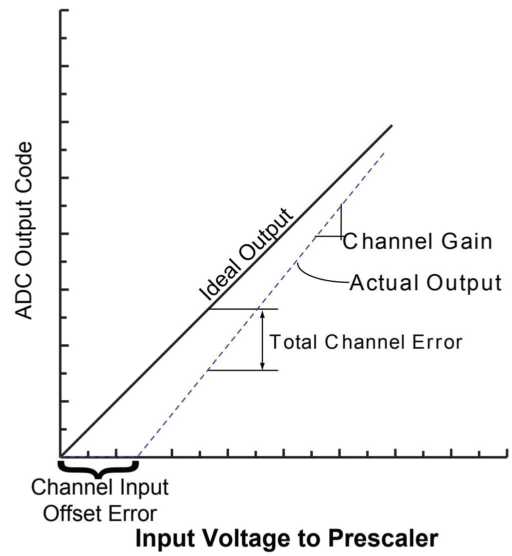

Figure 2-68 **• Total Channel Error Example**

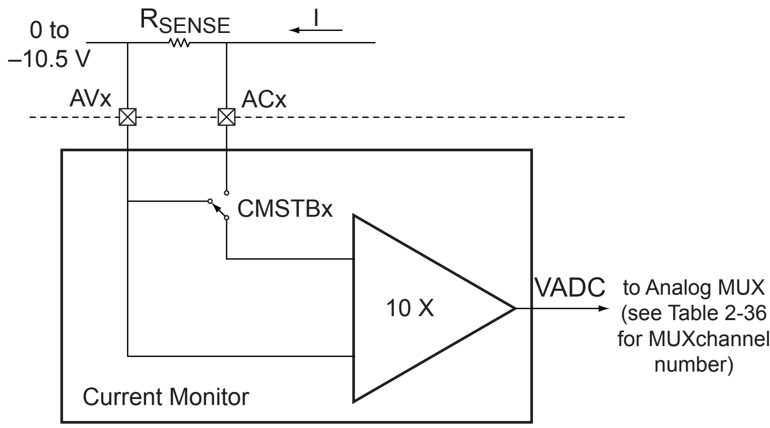

Figure 2-73 **• Negative Current Monitor**

Terminology

Accuracy

The accuracy of Fusion Current Monitor is ±2 mV minimum plus 5% of the differential voltage at the input. The input accuracy can be translated to error at the ADC output by using EQ 4. The 10 V/V gain is the gain of the Current Monitor Circuit, as described in the "Current Monitor" section on page 2-86. For 8-bit mode, N = 8, V_{AREF}= 2.56 V, zero differential voltage between AV and AC, the Error (E_{ADC}) is equal to 2 LSBs.

$$E_{ADC} = (2mV + 0.05|V_{AV} - V_{AC}|) \times (10V)/V \times \frac{2^N}{V_{AREF}}$$

EQ 4

where

N is the number of bits

V_{AREF} is the Reference voltage

V_{AV} is the voltage at AV pad

V_{AC} is the voltage at AC pad

Terminology

Resolution

Resolution defines the smallest temperature change Fusion Temperature Monitor can resolve. For ADC configured as 8-bit mode, each LSB represents 4°C, and 1°C per LSB for 10-bit mode. With 12-bit mode, the Temperature Monitor can still only resolve 1°C due to Temperature Monitor design.

Offset

The Fusion Temperature Monitor has a systematic offset (Table 2-49 on page 2-117), excluding error due to board resistance and ideality factor of the external diode. Microsemi provides an IP block (CalibIP) that is required in order to mitigate the systematic temperature offset. For further details on CalibIP, refer to the "*Temperature*, *Voltage, and Current Calibration in Fusion FPGAs" chapter of the Fusion FPGA Fabric User Guide.*

TUE – Total Unadjusted Error

TUE is a comprehensive specification that includes linearity errors, gain error, and offset error. It is the worst-case deviation from the ideal device performance. TUE is a static specification (Figure 2-87).

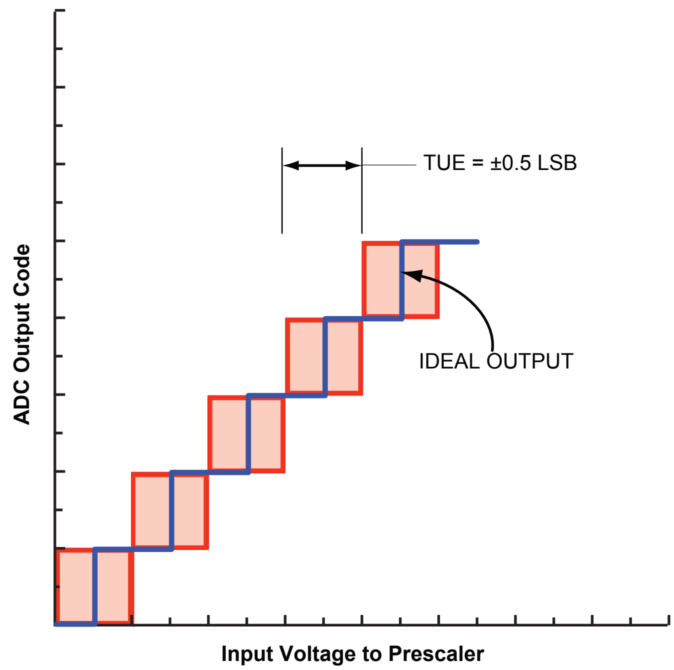

Figure 2-87 **• Total Unadjusted Error (TUE)**

ADC Operation

Once the ADC has powered up and been released from reset, ADCRESET, the ADC will initiate a calibration routine designed to provide optimal ADC performance. The Fusion ADC offers a robust calibration scheme to reduce integrated offset and linearity errors. The offset and linearity errors of the main capacitor array are compensated for with an 8-bit calibration capacitor array. The offset/linearity error calibration is carried out in two ways. First, a power-up calibration is carried out when the ADC comes out of reset. This is initiated by the CALIBRATE output of the Analog Block macro and is a fixed number of ADC_CLK cycles (3,840 cycles), as shown in Figure 2-89 on page 2-111. In this mode, the linearity and offset errors of the capacitors are calibrated.

To further compensate for drift and temperature-dependent effects, every conversion is followed by post-calibration of either the offset or a bit of the main capacitor array. The post-calibration ensures that, over time and with temperature, the ADC remains consistent.

After both calibration and the setting of the appropriate configurations, as explained above, the ADC is ready for operation. Setting the ADCSTART signal high for one clock period will initiate the sample and conversion of the analog signal on the channel as configured by CHNUMBER[4:0]. The status signals SAMPLE and BUSY will show when the ADC is sampling and converting (Figure 2-91 on page 2-112). Both SAMPLE and BUSY will initially go high. After the ADC has sampled and held the analog signal, SAMPLE will go low. After the entire operation has completed and the analog signal is converted, BUSY will go low and DATAVALID will go high. This indicates that the digital result is available on the RESULT[11:0] pins.

DATAVALID will remain high until a subsequent ADCSTART is issued. The DATAVALID goes low on the rising edge of SYSCLK as shown in Figure 2-90 on page 2-112. The RESULT signals will be kept constant until the ADC finishes the subsequent sample. The next sampled RESULT will be available when DATAVALID goes high again. It is ideal to read the RESULT when DATAVALID is '1'. The RESULT is latched and remains unchanged until the next DATAVLAID rising edge.

EQ 16 through EQ 18 can be used to calculate the acquisition time required for a given input. The STC signal gives the number of sample periods in ADCCLK for the acquisition time of the desired signal. If the actual acquisition time is higher than the STC value, the settling time error can affect the accuracy of the ADC, because the sampling capacitor is only partially charged within the given sampling cycle. Example acquisition times are given in Table 2-44 and Table 2-45. When controlling the sample time for the ADC along with the use of the active bipolar prescaler, current monitor, or temperature monitor, the minimum sample time(s) for each must be obeyed. EQ 19 can be used to determine the appropriate value of STC.

You can calculate the minimum actual acquisition time by using EQ 16:

$$VOUT = VIN(1 - e^{-t/RC})$$

EQ 16

For 0.5 LSB gain error, VOUT should be replaced with (VIN –(0.5 × LSB Value)):

$$(VIN - 0.5 \times LSB\ Value) = VIN(1 - e^{-t/RC})$$

EQ 17

where VIN is the ADC reference voltage (VREF)

Solving EQ 17:

$$t = RC \times \ln (VIN / (0.5 \times LSB\ Value))$$

EQ 18

where $R = Z_{INAD} + R_{SOURCE}$ and $C = C_{INAD}$.

Calculate the value of STC by using EQ 19.

$$t_{SAMPLE} = (2 + STC) \times (1 / ADCCLK) \text{ or } t_{SAMPLE} = (2 + STC) \times (\text{ADC Clock Period})$$

EQ 19

where ADCCLK = ADC clock frequency in MHz.

t_{SAMPLE} = 0.449 µs from bit resolution in Table 2-44.

ADC Clock frequency = 10 MHz or a 100 ns period.

STC = (t_{SAMPLE} / (1 / 10 MHz)) – 2 = 4.49 – 2 = 2.49.

You must round up to 3 to accommodate the minimum sample time.

***Table 2-44* • Acquisition Time Example with VAREF = 2.56 V**

VIN = 2.56V, R = 4K (R_{SOURCE} ~ 0), C = 18 pF		
Resolution	**LSB Value (mV)**	**Min. Sample/Hold Time for 0.5 LSB (µs)**
8	10	0.449
10	2.5	0.549
12	0.625	0.649

***Table 2-45* • Acquisition Time Example with VAREF = 3.3 V**

VIN = 3.3V, R = 4K (R_{SOURCE} ~ 0), C = 18 pF		
Resolution	**LSB Value (mV)**	**Min. Sample/Hold time for 0.5 LSB (µs)**
8	12.891	0.449
10	3.223	0.549
12	0.806	0.649

Sample Phase

A conversion is performed in three phases. In the first phase, the analog input voltage is sampled on the input capacitor. This phase is called sample phase. During the sample phase, the output signals BUSY and SAMPLE change from '0' to '1', indicating the ADC is busy and sampling the analog signal. The sample time can be controlled by input signals STC[7:0]. The sample time can be calculated by EQ 20. When controlling the sample time for the ADC along with the use of Prescaler or Current Monitor or Temperature Monitor, the minimum sample time for each must be obeyed.

Temporary overshoots are allowed according to Table 3-4 on page 3-4.

Solution 1

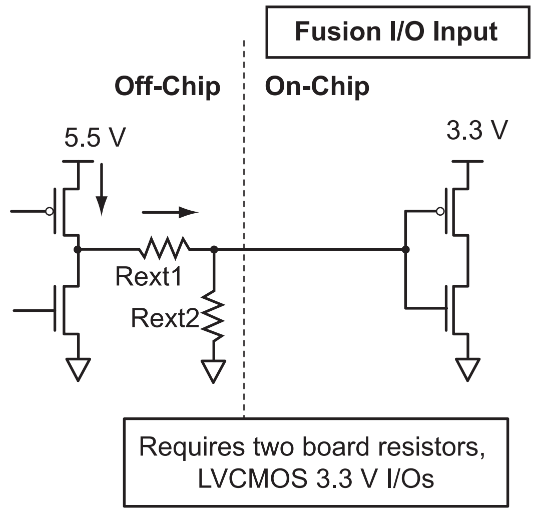

***Figure 2-103* • Solution 1**

Solution 2

The board-level design must ensure that the reflected waveform at the pad does not exceed limits provided in Table 3-4 on page 3-4. This is a long-term reliability requirement.

This scheme will also work for a 3.3 V PCI/PCI-X configuration, but the internal diode should not be used for clamping, and the voltage must be limited by the external resistors and Zener, as shown in Figure 2-104. Relying on the diode clamping would create an excessive pad DC voltage of 3.3 V + 0.7 V = 4 V.

Solution 2

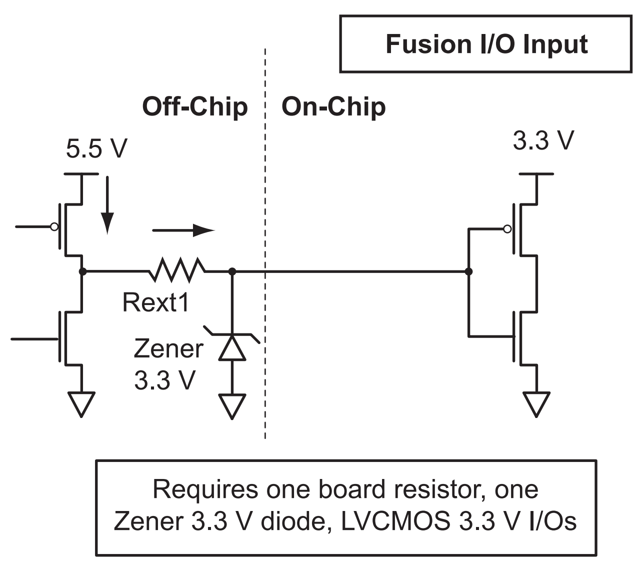

***Figure 2-104* • Solution 2**

User I/O Characteristics

Timing Model

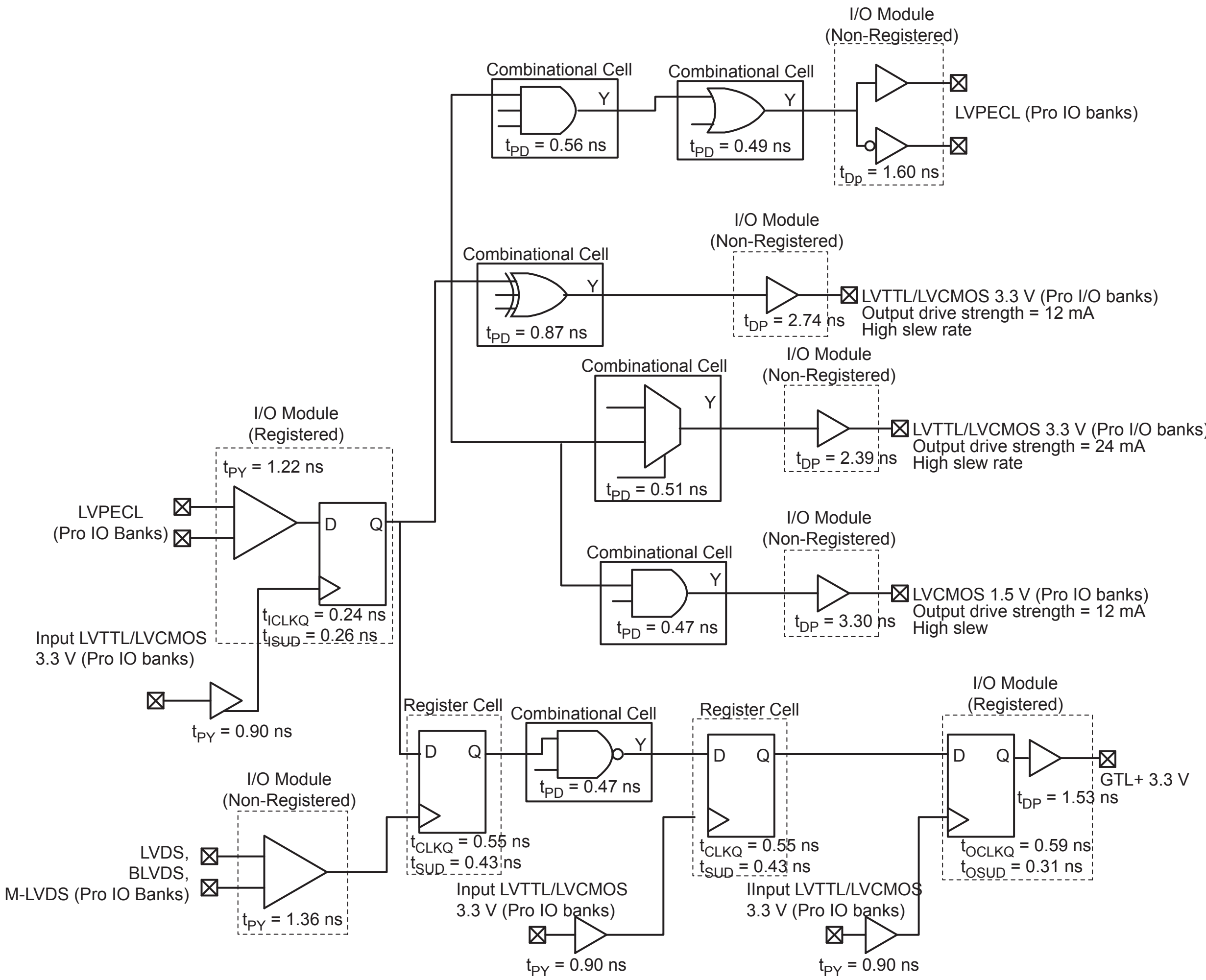

Figure 2-115 **• Timing Model**
Operating Conditions: –2 Speed, Commercial Temperature Range (T_J = 70°C), Worst-Case VCC = 1.425 V

**Table 2-93 • Summary of I/O Timing Characteristics – Software Default Settings
Commercial Temperature Range Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V,
Worst-Case VCCI = I/O Standard Dependent
Applicable to Advanced I/Os**

I/O Standard	Drive Strength (mA)	Slew Rate	Capacitive Load (pF)	External Resistor (Ohm)	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
3.3 V LVTTL/ 3.3 V LVCMOS	12 mA	High	35 pF	–	0.49	2.64	0.03	0.90	0.32	2.69	2.11	2.40	2.68	4.36	3.78	ns
2.5 V LVCMOS	12 mA	High	35 pF	–	0.49	2.66	0.03	0.98	0.32	2.71	2.56	2.47	2.57	4.38	4.23	ns
1.8 V LVCMOS	12 mA	High	35 pF	–	0.49	2.64	0.03	0.91	0.32	2.69	2.27	2.76	3.05	4.36	3.94	ns
1.5 V LVCMOS	12 mA	High	35 pF	–	0.49	3.05	0.03	1.07	0.32	3.10	2.67	2.95	3.14	4.77	4.34	ns
3.3 V PCI	Per PCI spec	High	10 pF	25 [2]	0.49	2.00	0.03	0.65	0.32	2.04	1.46	2.40	2.68	3.71	3.13	ns
3.3 V PCI-X	Per PCI-X spec	High	10 pF	25 [2]	0.49	2.00	0.03	0.62	0.32	2.04	1.46	2.40	2.68	3.71	3.13	ns
LVDS	24 mA	High	–	–	0.49	1.37	0.03	1.20	N/A	N/A	N/A	N/A	N/A	N/A	N/A	ns
LVPECL	24 mA	High	–	–	0.49	1.34	0.03	1.05	N/A	N/A	N/A	N/A	N/A	N/A	N/A	ns

Notes:

1. *For specific junction temperature and voltage-supply levels, refer to Table 3-6 on page 3-7 for derating values.*
2. *Resistance is used to measure I/O propagation delays as defined in PCI specifications. See Figure 2-123 on page 2-197 for connectivity. This resistor is not required during normal operation.*

**Table 2-94 • Summary of I/O Timing Characteristics – Software Default Settings
Commercial Temperature Range Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V,
Worst-Case VCCI = I/O Standard Dependent
Applicable to Standard I/Os**

I/O Standard	Drive Strength (mA)	Slew Rate	Capacitive Load (pF)	External Resistor (Ohm)	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
3.3 V LVTTL/ 3.3 V LVCMOS	8 mA	High	35 pF	–	0.49	3.29	0.03	0.75	0.32	3.36	2.80	1.79	2.01	ns
2.5 V LVCMOS	8 mA	High	35pF	–	0.49	3.56	0.03	0.96	0.32	3.40	3.56	1.78	1.91	ns
1.8 V LVCMOS	4 mA	High	35pF	–	0.49	4.74	0.03	0.90	0.32	4.02	4.74	1.80	1.85	ns
1.5 V LVCMOS	2 mA	High	35pF	–	0.49	5.71	0.03	1.06	0.32	4.71	5.71	1.83	1.83	ns

Note: For specific junction temperature and voltage-supply levels, refer to Table 3-6 on page 3-7 for derating values.

2.5 V LVCMOS

Low-Voltage CMOS for 2.5 V is an extension of the LVCMOS standard (JESD8-5) used for general-purpose 2.5 V applications.

Table 2-110 • Minimum and Maximum DC Input and Output Levels

2.5 V LVCMOS	VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL[1]	IIH[2]
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA[3]	Max. mA[3]	μA[4]	μA[4]
Applicable to Pro I/O Banks												
4 mA	–0.3	0.7	1.7	3.6	0.7	1.7	4	4	18	16	10	10
8 mA	–0.3	0.7	1.7	3.6	0.7	1.7	8	8	37	32	10	10
12 mA	–0.3	0.7	1.7	3.6	0.7	1.7	12	12	74	65	10	10
16 mA	–0.3	0.7	1.7	3.6	0.7	1.7	16	16	87	83	10	10
24 mA	–0.3	0.7	1.7	3.6	0.7	1.7	24	24	124	169	10	10
Applicable to Advanced I/O Banks												
2 mA	–0.3	0.7	1.7	2.7	0.7	1.7	2	2	18	16	10	10
4 mA	–0.3	0.7	1.7	2.7	0.7	1.7	4	4	18	16	10	10
6 mA	–0.3	0.7	1.7	2.7	0.7	1.7	6	6	37	32	10	10
8 mA	–0.3	0.7	1.7	2.7	0.7	1.7	8	8	37	32	10	10
12 mA	–0.3	0.7	1.7	2.7	0.7	1.7	12	12	74	65	10	10
16 mA	–0.3	0.7	1.7	2.7	0.7	1.7	16	16	87	83	10	10
24 mA	–0.3	0.7	1.7	2.7	0.7	1.7	24	24	124	169	10	10
Applicable to Standard I/O Banks												
2 mA	–0.3	0.7	1.7	3.6	0.7	1.7	2	2	18	16	10	10
4 mA	–0.3	0.7	1.7	3.6	0.7	1.7	4	4	18	16	10	10
6 mA	–0.3	0.7	1.7	3.6	0.7	1.7	6	6	37	32	10	10
8 mA	–0.3	0.7	1.7	3.6	0.7	1.7	8	8	37	32	10	10

Notes:

1. *IIL is the input leakage current per I/O pin over recommended operation conditions where –0.3 V < VIN < VIL.*
2. *IIH is the input leakage current per I/O pin over recommended operating conditions VIH < VIN < VCCI. Input current is larger when operating outside recommended ranges.*
3. *Currents are measured at high temperature (100°C junction temperature) and maximum voltage.*
4. *Currents are measured at 85°C junction temperature.*
5. *Software default selection highlighted in gray.*

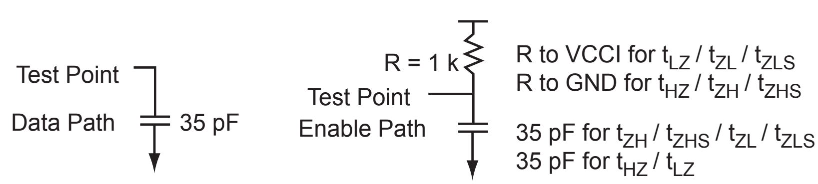

Figure 2-120 • AC Loading

Table 2-111 • AC Waveforms, Measuring Points, and Capacitive Loads

Input Low (V)	Input High (V)	Measuring Point* (V)	VREF (typ.) (V)	C_{LOAD} (pF)
0	2.5	1.2	–	35

Note: *Measuring point = Vtrip. See Table 2-90 on page 2-166 for a complete table of trip points.

I/O Register Specifications

Fully Registered I/O Buffers with Synchronous Enable and Asynchronous Preset

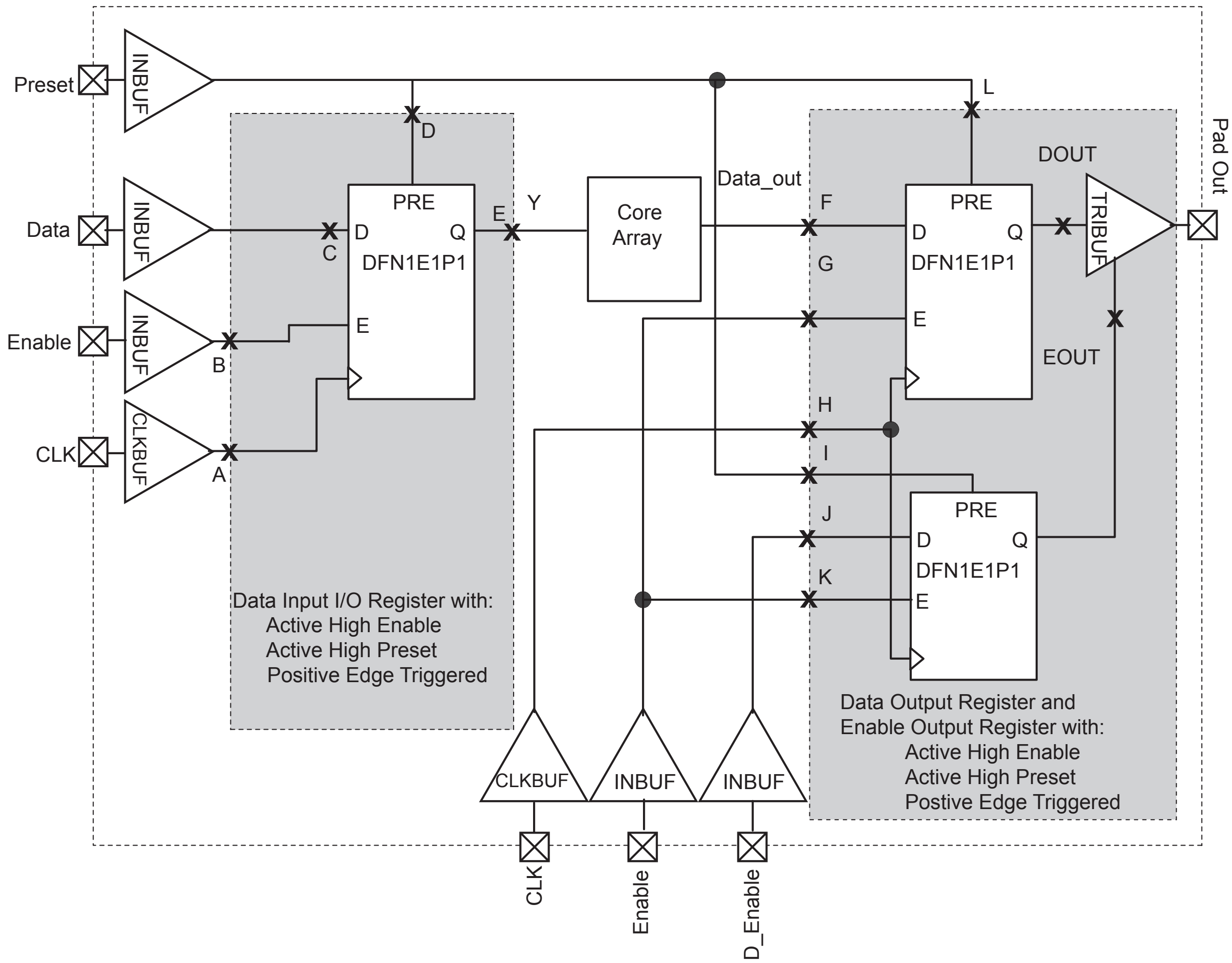

Figure 2-137 • Timing Model of Registered I/O Buffers with Synchronous Enable and Asynchronous Preset

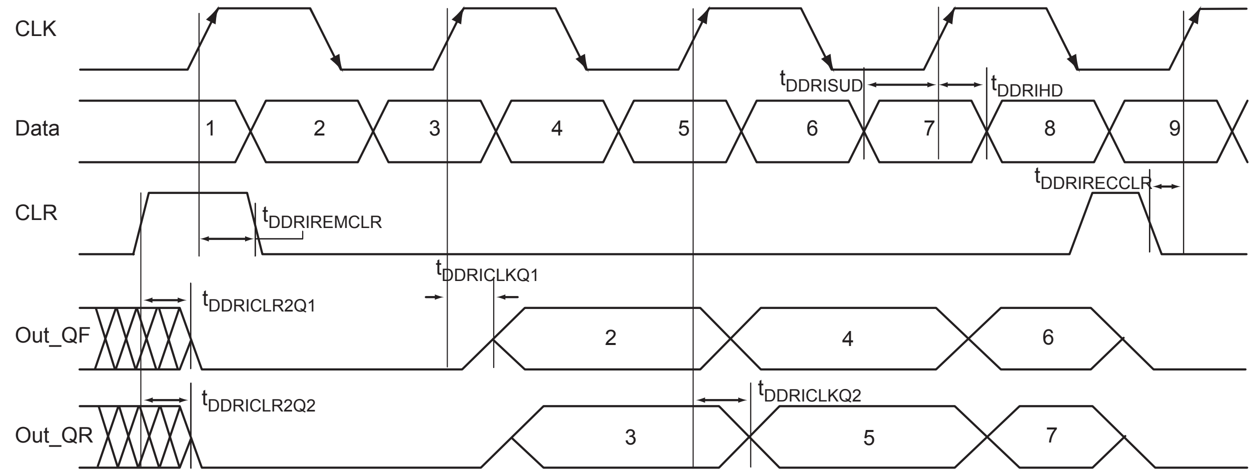

Figure 2-143 **• Input DDR Timing Diagram**

Timing Characteristics

Table 2-180 **• Input DDR Propagation Delays**
Commercial Temperature Range Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V

Parameter	Description	–2	–1	Std.	Units
$t_{DDRICLKQ1}$	Clock-to-Out Out_QR for Input DDR	0.39	0.44	0.52	ns
$t_{DDRICLKQ2}$	Clock-to-Out Out_QF for Input DDR	0.27	0.31	0.37	ns
$t_{DDRISUD}$	Data Setup for Input DDR	0.28	0.32	0.38	ns
t_{DDRIHD}	Data Hold for Input DDR	0.00	0.00	0.00	ns
$t_{DDRICLR2Q1}$	Asynchronous Clear-to-Out Out_QR for Input DDR	0.57	0.65	0.76	ns
$t_{DDRICLR2Q2}$	Asynchronous Clear-to-Out Out_QF for Input DDR	0.46	0.53	0.62	ns
$t_{DDRIREMCLR}$	Asynchronous Clear Removal Time for Input DDR	0.00	0.00	0.00	ns
$t_{DDRIRECCLR}$	Asynchronous Clear Recovery Time for Input DDR	0.22	0.25	0.30	ns
$t_{DDRIWCLR}$	Asynchronous Clear Minimum Pulse Width for Input DDR	0.22	0.25	0.30	ns
$t_{DDRICKMPWH}$	Clock Minimum Pulse Width High for Input DDR	0.36	0.41	0.48	ns
$t_{DDRICKMPWL}$	Clock Minimum Pulse Width Low for Input DDR	0.32	0.37	0.43	ns
$F_{DDRIMAX}$	Maximum Frequency for Input DDR	1404	1232	1048	MHz

Note: For the derating values at specific junction temperature and voltage supply levels, refer to Table 3-7 on page 3-9.

Pin Descriptions

Supply Pins

GND **Ground**

Ground supply voltage to the core, I/O outputs, and I/O logic.

GNDQ **Ground (quiet)**

Quiet ground supply voltage to input buffers of I/O banks. Within the package, the GNDQ plane is decoupled from the simultaneous switching noise originated from the output buffer ground domain. This minimizes the noise transfer within the package and improves input signal integrity. GNDQ needs to always be connected on the board to GND. Note: In FG256, FG484, and FG676 packages, GNDQ and GND pins are connected within the package and are labeled as GND pins in the respective package pin assignment tables.

ADCGNDREF **Analog Reference Ground**

Analog ground reference used by the ADC. This pad should be connected to a quiet analog ground.

GNDA **Ground (analog)**

Quiet ground supply voltage to the Analog Block of Fusion devices. The use of a separate analog ground helps isolate the analog functionality of the Fusion device from any digital switching noise. A 0.2 V maximum differential voltage between GND and GNDA/GNDQ should apply to system implementation.

GNDAQ **Ground (analog quiet)**

Quiet ground supply voltage to the analog I/O of Fusion devices. The use of a separate analog ground helps isolate the analog functionality of the Fusion device from any digital switching noise. A 0.2 V maximum differential voltage between GND and GNDA/GNDQ should apply to system implementation. Note: In FG256, FG484, and FG676 packages, GNDAQ and GNDA pins are connected within the package and are labeled as GNDA pins in the respective package pin assignment tables.

GNDNVM **Flash Memory Ground**

Ground supply used by the Fusion device's flash memory block module(s).

GNDOSC **Oscillator Ground**

Ground supply for both integrated RC oscillator and crystal oscillator circuit.

VCC15A **Analog Power Supply (1.5 V)**

1.5 V clean analog power supply input for use by the 1.5 V portion of the analog circuitry.

VCC33A **Analog Power Supply (3.3 V)**

3.3 V clean analog power supply input for use by the 3.3 V portion of the analog circuitry.

VCC33N **Negative 3.3 V Output**

This is the –3.3 V output from the voltage converter. A 2.2 µF capacitor must be connected from this pin to ground.

VCC33PMP **Analog Power Supply (3.3 V)**

3.3 V clean analog power supply input for use by the analog charge pump. To avoid high current draw, VCC33PMP should be powered up simultaneously with or after VCC33A.

VCCNVM **Flash Memory Block Power Supply (1.5 V)**

1.5 V power supply input used by the Fusion device's flash memory block module(s). To avoid high current draw, VCC should be powered up before or simultaneously with VCCNVM.

VCCOSC **Oscillator Power Supply (3.3 V)**

Power supply for both integrated RC oscillator and crystal oscillator circuit. The internal 100 MHz oscillator, powered by the VCCOSC pin, is needed for device programming, operation of the VDDN33 pump, and eNVM operation. VCCOSC is off only when VCCA is off. VCCOSC must be powered whenever the Fusion device needs to function.

TMS **Test Mode Select**

The TMS pin controls the use of the IEEE1532 boundary scan pins (TCK, TDI, TDO, TRST). There is an internal weak pull-up resistor on the TMS pin.

TRST **Boundary Scan Reset Pin**

The TRST pin functions as an active low input to asynchronously initialize (or reset) the boundary scan circuitry. There is an internal weak pull-up resistor on the TRST pin. If JTAG is not used, an external pull-down resistor could be included to ensure the TAP is held in reset mode. The resistor values must be chosen from Table 2-183 and must satisfy the parallel resistance value requirement. The values in Table 2-183 correspond to the resistor recommended when a single device is used and to the equivalent parallel resistor when multiple devices are connected via a JTAG chain.

In critical applications, an upset in the JTAG circuit could allow entering an undesired JTAG state. In such cases, Microsemi recommends tying off TRST to GND through a resistor placed close to the FPGA pin.

Note that to operate at all VJTAG voltages, 500 Ω to 1 kΩ will satisfy the requirements.

Special Function Pins

NC **No Connect**

This pin is not connected to circuitry within the device. These pins can be driven to any voltage or can be left floating with no effect on the operation of the device.

DC **Don't Connect**

This pin should not be connected to any signals on the PCB. These pins should be left unconnected.

NCAP **Negative Capacitor**

Negative Capacitor is where the negative terminal of the charge pump capacitor is connected. A capacitor, with a 2.2 µF recommended value, is required to connect between PCAP and NCAP.

PCAP **Positive Capacitor**

Positive Capacitor is where the positive terminal of the charge pump capacitor is connected. A capacitor, with a 2.2 µF recommended value, is required to connect between PCAP and NCAP.

PUB **Push Button**

Push button is the connection for the external momentary switch used to turn on the 1.5 V voltage regulator and can be floating if not used.

PTBASE **Pass Transistor Base**

Pass Transistor Base is the control signal of the voltage regulator. This pin should be connected to the base of the external pass transistor used with the 1.5 V internal voltage regulator and can be floating if not used.

PTEM **Pass Transistor Emitter**

Pass Transistor Emitter is the feedback input of the voltage regulator.

This pin should be connected to the emitter of the external pass transistor used with the 1.5 V internal voltage regulator and can be floating if not used.

XTAL1 **Crystal Oscillator Circuit Input**

Input to crystal oscillator circuit. Pin for connecting external crystal, ceramic resonator, RC network, or external clock input. When using an external crystal or ceramic oscillator, external capacitors are also recommended (Please refer to the crystal oscillator manufacturer for proper capacitor value).

If using external RC network or clock input, XTAL1 should be used and XTAL2 left unconnected. In the case where the Crystal Oscillator block is not used, the XTAL1 pin should be connected to GND and the XTAL2 pin should be left floating.

PQ208		
Pin Number	AFS250 Function	AFS600 Function
147	GCC1/IO47PDB1V0	IO39NDB2V0
148	IO42NDB1V0	GCA2/IO39PDB2V0
149	GBC2/IO42PDB1V0	IO31NDB2V0
150	VCCIB1	GBB2/IO31PDB2V0
151	GND	IO30NDB2V0
152	VCC	GBA2/IO30PDB2V0
153	IO41NDB1V0	VCCIB2
154	GBB2/IO41PDB1V0	GNDQ
155	IO40NDB1V0	VCOMPLB
156	GBA2/IO40PDB1V0	VCCPLB
157	GBA1/IO39RSB0V0	VCCIB1
158	GBA0/IO38RSB0V0	GNDQ
159	GBB1/IO37RSB0V0	GBB1/IO27PPB1V1
160	GBB0/IO36RSB0V0	GBA1/IO28PPB1V1
161	GBC1/IO35RSB0V0	GBB0/IO27NPB1V1
162	VCCIB0	GBA0/IO28NPB1V1
163	GND	VCCIB1
164	VCC	GND
165	GBC0/IO34RSB0V0	VCC
166	IO33RSB0V0	GBC1/IO26PDB1V1
167	IO32RSB0V0	GBC0/IO26NDB1V1
168	IO31RSB0V0	IO24PPB1V1
169	IO30RSB0V0	IO23PPB1V1
170	IO29RSB0V0	IO24NPB1V1
171	IO28RSB0V0	IO23NPB1V1
172	IO27RSB0V0	IO22PPB1V0
173	IO26RSB0V0	IO21PPB1V0
174	IO25RSB0V0	IO22NPB1V0
175	VCCIB0	IO21NPB1V0
176	GND	IO20PSB1V0
177	VCC	IO19PSB1V0
178	IO24RSB0V0	IO14NSB0V1
179	IO23RSB0V0	IO12PDB0V1
180	IO22RSB0V0	IO12NDB0V1
181	IO21RSB0V0	VCCIB0
182	IO20RSB0V0	GND
183	IO19RSB0V0	VCC

PQ208		
Pin Number	AFS250 Function	AFS600 Function
184	IO18RSB0V0	IO10PPB0V1
185	IO17RSB0V0	IO09PPB0V1
186	IO16RSB0V0	IO10NPB0V1
187	IO15RSB0V0	IO09NPB0V1
188	VCCIB0	IO08PPB0V1
189	GND	IO07PPB0V1
190	VCC	IO08NPB0V1
191	IO14RSB0V0	IO07NPB0V1
192	IO13RSB0V0	IO06PPB0V0
193	IO12RSB0V0	IO05PPB0V0
194	IO11RSB0V0	IO06NPB0V0
195	IO10RSB0V0	IO04PPB0V0
196	IO09RSB0V0	IO05NPB0V0
197	IO08RSB0V0	IO04NPB0V0
198	IO07RSB0V0	GAC1/IO03PDB0V0
199	IO06RSB0V0	GAC0/IO03NDB0V0
200	GAC1/IO05RSB0V0	VCCIB0
201	VCCIB0	GND
202	GND	VCC
203	VCC	GAB1/IO02PDB0V0
204	GAC0/IO04RSB0V0	GAB0/IO02NDB0V0
205	GAB1/IO03RSB0V0	GAA1/IO01PDB0V0
206	GAB0/IO02RSB0V0	GAA0/IO01NDB0V0
207	GAA1/IO01RSB0V0	GNDQ
208	GAA0/IO00RSB0V0	VCCIB0

Revision	Changes	Page
Advance v1.5 (continued)	This bullet was added to the "Integrated A/D Converter (ADC) and Analog I/O" section: ADC Accuracy is Better than 1%	I
	In the "Integrated Analog Blocks and Analog I/Os" section, ±4 LSB was changed to 0.72. The following sentence was deleted: The input range for voltage signals is from –12 V to +12 V with full-scale output values from 0.125 V to 16 V. In addition, 2°C was changed to 3°C: "One analog input in each quad can be connected to an external temperature monitor diode and achieves detection accuracy of ±3ºC." The following sentence was deleted: The input range for voltage signals is from –12 V to +12 V with full-scale output values from 0.125 V to 16 V.	1-4
	The title of the datasheet changed from Actel Programmable System Chips to Actel Fusion Mixed Signal FPGAs. In addition, all instances of programmable system chip were changed to mixed signal FPGA.	N/A
Advance v1.4 (July 2008)	In Table 3-8 · Quiescent Supply Current Characteristics (IDDQ)1, footnote references were updated for I_{DC2} and I_{DC3}. Footnote 3 and 4 were updated and footnote 5 is new.	3-11
Advance v1.3 (July 2008)	The "ADC Description" section was significantly updated. Please review carefully.	2-102
Advance v1.2 (May 2008)	Table 2-25 • Flash Memory Block Timing was significantly updated.	2-55
	The "V_{AREF} Analog Reference Voltage" pin description section was significantly update. Please review it carefully.	2-226
	Table 2-45 • ADC Interface Timing was significantly updated.	2-110
	Table 2-56 • Direct Analog Input Switch Control Truth Table—AV (x = 0), AC (x = 1), and AT (x = 3) was significantly updated.	2-131
	The following sentence was deleted from the "Voltage Monitor" section: The Analog Quad inputs are tolerant up to 12 V + 10%.	2-86
	The "180-Pin QFN" figure was updated. D1 to D4 are new and the figure was changed to bottom view. The note below the figure is new.	3-3
Advance v1.1 (May 2008)	The following text was incorrect and therefore deleted: **VCC33A** **Analog Power Filter** Analog power pin for the analog power supply low-pass filter. An external 100 pF capacitor should be connected between this pin and ground. There is still a description of V_{CC33A} on page 2-224.	2-204